

LIST OF CLAIMS

1- 12. (Cancelled)

13. (Previously Presented) An insulated gate transistor having a gate electrode on a substrate with a gate insulator interposed therebetween, wherein the gate insulator including silicon and oxygen contains both nitrogen atoms and halogen atoms, and wherein nitrogen atom concentration of the gate insulator is within a range of $1 \times 10^{18} \text{ cm}^{-3}$ - $1 \times 10^{20} \text{ cm}^{-3}$ and maximum fluorine atom concentration of the gate insulator is within a range of $1 \times 10^{18} \text{ cm}^{-3}$ - $6 \times 10^{19} \text{ cm}^{-3}$.

14. (Cancelled)

15. (Cancelled)

16. (Previously Presented) The insulated gate transistor according to claim 13, wherein the gate electrode contains boron, and the boron does not diffuse into the substrate.

17. (Cancelled)

18. (Cancelled)

19. (Previously Presented) The insulated gate transistor according to claim 13, wherein the gate insulator has a film thickness of about 0.5-5 nm.

20. (Cancelled)

21. (Cancelled)

22. (Previously Presented) The insulated gate transistor according to claim 13, wherein the gate electrode comprises a polycrystalline material that is at least one selected from the group consisting of polysilicon, polycrystalline germanium and polysilicon germanium.

23. (Cancelled)

24. (Cancelled)